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Hatakeyama

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(54) **CHEMICALLY AMPLIFIED RESIST COMPOSITION AND PATTERNING PROCESS**

(71) Applicant: **SHIN-ETSU CHEMICAL CO., LTD.**, Tokyo (JP)

(72) Inventor: **Jun Hatakeyama**, Joetsu (JP)

(73) Assignee: **SHIN-ETSU CHEMICAL CO., LTD.**, Tokyo (JP)

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See application file for complete search history.

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Primary Examiner — John S Chu

(74) *Attorney, Agent, or Firm* — Westerman, Hattori, Daniels & Adrian, LLP

(57) **ABSTRACT**

A chemically amplified resist composition comprising a base polymer, an acid generator, and a specific oxime compound has a high contrast of alkaline dissolution rate before and after exposure and high resolution and forms a pattern of satisfactory profile with minimal roughness and wide focus margin.

12 Claims, No Drawings